

EAST Search History

S28	43	facet with si\$2N and (semiconductor near laser) and @ad <"20011106"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 17:12
S29	43	(facet with si\$2N) and (semiconductor near laser) and @ad <"20011106"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 17:28
S30	54	(facet with amorphous) and (semiconductor near laser) and @ad <"20011106"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 21:07
S31	15	(facet with amorphous) and (semiconductor near laser) and @ad <"20011106" and (nitrogen nitro)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 21:12
S32	22	(facet with amorphous) and (semiconductor near laser) and @ad <"20011106" and (nitrogen nitro nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 22:01
S33	12	(facet with amorphous) and (semiconductor near laser) and @ad <"20011106" and (nitrogen nitro nitride) and Ga\$As and Ga\$al\$as	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 21:13
S34	3	("4280107" "5892786" "RE37354").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/19 22:00
S35	16	(facet with amorphous) and (semiconductor near laser) and @ad <"20011106" and (nitrogen nitro nitride) and (ratio with (Si and H)(silicon and hydrogen))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 22:02
S36	2	(facet with amorphous) and (semiconductor near laser) and @ad <"20011106" and (nitrogen nitro nitride) and (ratio with ((Si and H)(silicon and hydrogen)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 22:02
S37	111	(Si\$1N\$1\$H\$1 with (facet\$2 coat\$4)) and @ad <"20011106" and ratio	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/11 18:06

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S38	152	(Si\$1N\$1\$H\$1 with (facet\$2 coat\$4)) and @ad <"20011106" and (ratio near\$3 Si\$2N\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/11 15:01
S39	130	(Si\$1N\$1\$H\$1 with (facet\$2 coat\$4)) and @ad <"20011106" and (ratio near\$3 Si\$1N\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/11 15:01
S40	5	(Si\$1N\$1\$H\$1 near (facet\$2 coat\$4)) and @ad <"20011106" and (ratio near\$3 Si\$1N\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/11 17:26
S41	2	("20040151226").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/11 16:40
S42	2	("20050135439").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/11 16:40
S43	1	(Si\$1N\$1\$H\$1 near (facet\$2 coat\$4)) and @ad <"20011106" and (ratio with Si\$1N\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/11 17:27
S44	3	(Si\$1N\$1\$H\$1 near (facet\$2 coat\$4)) and (ratio with Si\$1N\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/11 17:27
S45	0	(Si\$1N\$1\$H\$1 with (facet\$2 coat\$4)) and @ad <"20011106" and (Si\$1N near ratio)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/11 18:08
S46	4	(Si\$1N\$1\$H\$1 with (facet\$2 coat\$4)) and @ad <"20011106" and (Si\$1N near8 ratio)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/11 18:09
S47	4	(Si\$1N\$1\$H\$1 with (facet\$2 coat\$4)) and @ad <"20011106" and (Si\$1N with ratio)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/11 18:12

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S48	41600	Si\$2N\$2H\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/11 18:12
S49	2242	Si\$2N\$2H\$2 and (Si\$2N\$2 with ratio)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/11 18:14
S50	68	Si\$2N\$2H\$2 and (Si\$2N\$2 with ratio) and (semiconductor near laser)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/13 18:56